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Spin–Orbit and Zeeman Effects on the Electronic Properties of Single Quantum Rings: Applied Magnetic Field and Topological Defects

José C. León-González ^{1,2}, Rafael G. Toscano-Negrette ^{1,2}, A. L. Morales ¹, J. A. Vinasco ¹, M. B. Yücel ³, H. Sari ⁴, E. Kasapoglu ⁵, S. Sakiroglu ⁶, M. E. Mora-Ramos ⁷, R. L. Restrepo ⁸ and C. A. Duque ^{1,*}

- ¹ Grupo de Materia Condensada-UdeA, Instituto de Física, Facultad de Ciencias Exactas y Naturales, Universidad de Antioquia UdeA, Calle 70 No. 52-21, Medellín 050010, Colombia; jose.leong@udea.edu.co (J.C.L.-G.); alvaro.morales@udea.edu.co (A.L.M.); juan.vinasco@udea.edu.co (J.A.V.)
 - ² Departamento de Física y Electrónica, Universidad de Córdoba, Carrera 6 No. 77-305, Montería 230002, Colombia
 - ³ Department of Physics, Faculty of Science, Akdeniz University, 07058 Antalya, Turkey; myucel@akdeniz.edu.tr
 - ⁴ Department of Mathematical and Natural Science, Faculty of Education, Sivas Cumhuriyet University, 58140 Sivas, Turkey; sari@cumhuriyet.edu.tr
 - ⁵ Department of Physics, Faculty of Science, Sivas Cumhuriyet University, 58140 Sivas, Turkey; ekasap@cumhuriyet.edu.tr
 - ⁶ Dokuz Eylül University, Faculty of Science, Physics Department, 35390 Izmir, Turkey; serpil.sakiroglu@deu.edu.tr
 - ⁷ Centro de Investigación en Ciencias, Instituto de Investigación en Ciencias Básicas y Aplicadas, Universidad Autónoma del Estado de Morelos, Av. Universidad 1001, Cuernavaca CP 62209, Morelos, Mexico; memora@uaem.mx
 - ⁸ Universidad EIA, Envigado 055428, Colombia; ricardo.restrepo@eia.edu.co
- * Correspondence: carlos.duque1@udea.edu.co



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Abstract: Within the framework of effective mass theory, we investigate the effects of spin–orbit interaction (SOI) and Zeeman splitting on the electronic properties of an electron confined in GaAs single quantum rings. Energies and envelope wavefunctions in the system are determined by solving the Schrödinger equation via the finite element method. First, we consider an inversely quadratic model potential to describe electron confining profiles in a single quantum ring. The study also analyzes the influence of applied electric and magnetic fields. Solutions for eigenstates are then used to evaluate the linear inter-state light absorption coefficient through the corresponding resonant transition energies and electric dipole matrix moment elements, assuming circular polarization for the incident radiation. Results show that both SOI effects and Zeeman splitting reduce the absorption intensity for the considered transitions compared to the case when these interactions are absent. In addition, the magnitude and position of the resonant peaks have non-monotonic behavior with external magnetic fields. Secondly, we investigate the electronic and optical properties of the electron confined in the quantum ring with a topological defect in the structure; the results show that the crossings in the energy curves as a function of the magnetic field are eliminated, and, therefore, an improvement in transition energies occurs. In addition, the dipole matrix moments present a non-oscillatory behavior compared to the case when a topological defect is not considered.

Keywords: spin–orbit interaction; Zeeman splitting; circularly polarized light; topological defect; optical absorption coefficient

1. Introduction

The study of low-dimensional semiconductor heterostructures has attracted much attention from the scientific community due to their novel and prospective applications. Varying